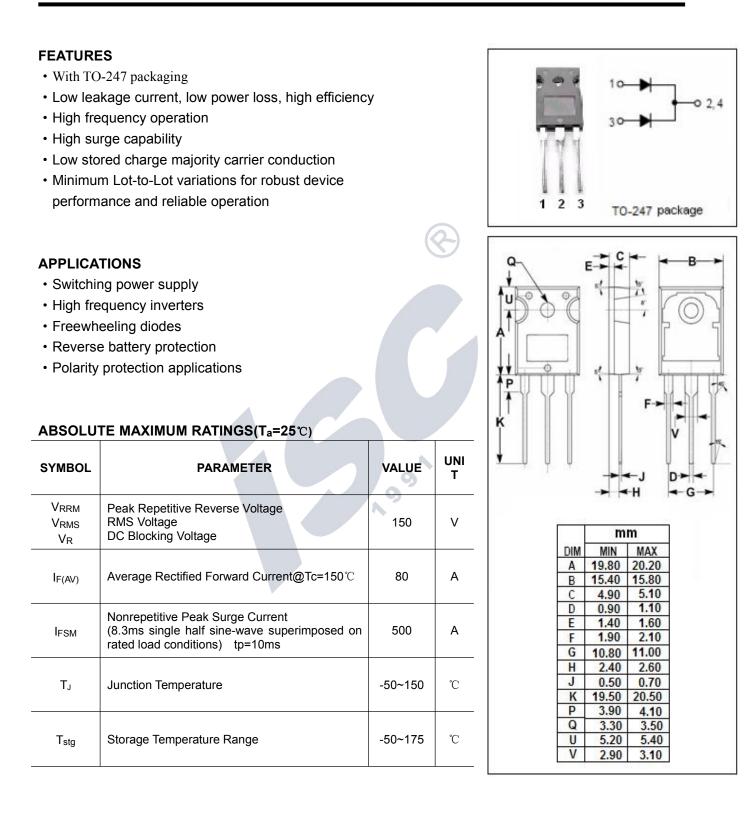


INCHANGE SEMICONDUCTOR

Schottky Barrier Rectifier

STPS80150CW



Schottky Barrier Rectifier

STPS80150CW

THERMAL CHARACTERISTICS

SYMBO	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	0.7	°C/W

ELECTRICAL CHARACTERISTICS (Pulse Test: Pulse Width=300 µ s,Duty Cycle≤1%)

SYMBOL	PARAMETER	CONDITIONS	МАХ	UNIT
VF	Maximum Instantaneous Forward Voltage	I _F = 40A ;Tc= 25 ℃ I _F = 40A ;Tc=125 ℃ I _F = 80A ;Tc= 25 ℃ I _F = 80A ;Tc=125 ℃	0.84 0.74 0.96 0.86	V
I _R	Maximum Instantaneous Reverse Current	V _R = rated V _{RRM} ;Tc= 25℃ V _R = rated V _{RRM} ;Tc=125℃	0.03 20	mA

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